



### SINGLE CHANNEL SMART LOAD SWITCH

## **Description and Applications**

The DML3009LDC load switch provides a component and areareducing solution for efficient power domain switching with inrush current limit via soft-start. In addition to integrated control functionality with ultra-low on-resistance, this device offers system safeguards and monitoring via fault protection and power good signaling. This costeffective solution is ideal for power management and hot-swap applications requiring low power consumption in a small footprint.

## Applications

- Portable Electronics and Systems
- Notebook and Tablet Computers
- Telecom, Networking, Medical, and Industrial Equipment
- Set-Top Boxes, Servers, and Gateways
- Hot-Swap Devices and Peripheral Ports

## **Features and Benefits**

- Advanced Controller with ChargePump
- Integrated N-Channel MOSFET with Ultra-Low R<sub>ON</sub>
- Input Voltage Range 0.5V to 13.5V
- Soft-Start via Controlled Slew Rate
- Adjustable Slew Rate Control
- Power Good Signal
- Thermal Shutdown
- V<sub>IN</sub> Undervoltage Lockout
- Short-Circuit Protection
- Extremely Low Standby Current
- Load Bleed (Quick Discharge)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

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Top View

#### V-DFN3030-12 (Type B)





Top View

## Ordering Information (Note 4)

| Part Number  | Case                  | Packaging        |
|--------------|-----------------------|------------------|
| DML3009LDC-7 | V-DFN3030-12 (Type B) | 3000/Tape & Reel |

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**

Notes:

#### V-DFN3030-12 (Type B)



LS39 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



# **Typical Application Circuit**



# **Pin Description**

| Pin Number | Pin Name         | Pin Function  |  |
|------------|------------------|---|--|
| 1, 13      | V <sub>IN</sub>  | Drain of MOSFET (0.5V to 13.5V). Pin 1 must be connected to Pin 13.   |  |
| 2          | EN               | Active-high digital input used to turn on the MOSFET, pin has an internal pull down resistor to GND   |  |
| 3          | V <sub>CC</sub>  | Supply voltage to controller (3.0V to 5.5V).  |  |
| 4          | GND              | Controller ground.  |  |
| 5          | SR               | Slew rate adjustment; Please refer C <sub>SR</sub> vs. V <sub>OUT</sub> rising time table.  |  |
| 6          | PG               | Active-high, open-drain output that indicates when the gate of the MOSFET is fully charged, external pull up resistor $\ge 1 k\Omega$ to an external voltage source required; tie to GND if not used. |  |
| 7          | BLEED            | Load bleed connection, must be tied to V <sub>OUT</sub> either directly or through a resistor $\leq 1k\Omega$ .   |  |
| 8 to 12    | V <sub>OUT</sub> | Source of MOSFET connected toload.  |  |

# **Function Block Diagram**





# Absolute Maximum Rating

| Parameter  | Rating          |  |
|--|-----------------|--|
| V <sub>IN</sub> , BLEED, V <sub>OUT</sub> to GND | -0.3V to 18V    |  |
| EN, V <sub>CC</sub> , SR, PG to GND              | -0.3V to 6V     |  |
| I <sub>MAX</sub>                                 | 20A             |  |
| Junction Temperature (T <sub>J</sub> )           | +150°C          |  |
| Storage Temperature (T <sub>S</sub> )            | -65°C to +150°C |  |

# **Recommended Operating Ranges**

| Parameter                                    | Rating         |
|--|----------------|
| Supply Voltage (V <sub>VCC</sub> )           | 3V to 5.5V     |
| Input Voltage (V <sub>VIN</sub> )            | 0.5V to 13.5V  |
| Ambient Temperature (T <sub>A</sub> )        | -40°C to +85°C |
| Package Thermal Resistance ( $\Theta_{JC}$ ) | 3.5°C/W        |
| Package Thermal Resistance ( $\Theta_{JA}$ ) | 30°C/W         |

**Electrical Characeristics** ( $T_A = +25^{\circ}C$ ,  $V_{VCC}=3.3V$ ,  $V_{VIN}=5V=V_{TERM}$ ,  $C_{VIN}=1\mu$ F,  $C_{VOUT}=0.1\mu$ F,  $C_{VCC}=1\mu$ F,  $C_{SR}=1n$ F, unless otherwise specified.)

| Symbol                                 | Parameter  | Conditions  | Min  | Тур  | Max  | Unit |
|--|--|---|------|------|------|------|
| V <sub>VIN</sub>                       | Input Voltage                                    | —   | 0.5  |      | 13.5 | V    |
| V <sub>VCC</sub>                       | Supply Voltage                                   | —   | 3.0  |      | 5.5  | V    |
|  | V. Durania Quanta Quanta                         | $V_{EN} = V_{VCC} = 3V, V_{VIN} = 12V$                            | —    | 310  | 400  | μA   |
| IDYN                                   | V <sub>CC</sub> Dynamic Supply Current           | V <sub>EN</sub> =V <sub>VCC</sub> = 5.5V, V <sub>VIN</sub> = 1.8V | —    | 510  | 750  | μA   |
| 1                                      | V Chutdaura Curanha Curant                       | $V_{VCC} = 3V, V_{EN} = 0V$                                       | —    | 0.1  | 1    | μA   |
| ISTBY                                  | V <sub>CC</sub> Shutdown Supply Current          | $V_{VCC} = 5.5V, V_{EN} = 0V$                                     | —    | 0.1  | 2    | μA   |
| V <sub>ENH</sub>                       | EN High Level Voltage                            | $V_{VCC} = 3V$ to 5.5V  | 2.0  | _    | _    | V    |
| V <sub>ENL</sub>                       | EN Low Level Voltage                             | $V_{VCC} = 3V$ to 5.5V  | _    | _    | 0.8  | V    |
| D                                      | Pland Desistance                                 | $V_{VCC} = 3V, V_{EN} = 0V$                                       | 86   | 108  | 130  | Ω    |
| RBLEED                                 | Bleed Resistance                                 | $V_{VCC} = 5.5V, V_{EN} = 0V$                                     | 64   | 80   | 100  | Ω    |
|  | Diagd Dia Lookana Comant                         | $V_{VCC} = V_{EN} = 3V, V_{VIN} = 1.8V$                           | —    | 20   | 45   | μA   |
| IBLEED                                 | Bleed Pin Leakage Current                        | $V_{VCC} = V_{EN} = 3V, V_{VIN} = 12V$                            |      | 50   | 70   | μA   |
| V <sub>PGL</sub>                       | PG Output Low Voltage                            | $V_{VCC} = 3V; I_{SINK} = 5mA$                                    | —    |      | 0.2  | V    |
| I <sub>PG</sub>                        | PG Output Leakage Current                        | $V_{VCC} = 3V; V_{TERM} = 3.3V$                                   | —    |      | 100  | nA   |
| Switching D                            | Device   |   |      |      |      |      |
|  | V <sub>VCC</sub> = 3.3V, V <sub>VIN</sub> = 1.8V | _   | 6.1  | 9    | mΩ   |      |
|  |  | V <sub>VCC</sub> = 3.3V, V <sub>VIN</sub> = 5V                    | —    | 5.9  | 8    | mΩ   |
| Davi                                   | Switch On State Registered                       | V <sub>VCC</sub> = 3.3V, V <sub>VIN</sub> = 12V                   | —    | 5.8  | 8    | mΩ   |
| RON                                    | Switch On-State Resistance                       | $V_{VCC} = 5V, V_{VIN} = 1.8V$                                    | _    | 4.8  | 7    | mΩ   |
|  |  | $V_{VCC} = 5V, V_{VIN} = 5V$                                      | _    | 4.8  | 7    | mΩ   |
|  |  | $V_{VCC} = 5V, V_{VIN} = 12V$                                     | _    | 4.8  | 7    | mΩ   |
| I <sub>LEAK</sub>                      | Input Shutdown Supply Current                    | $V_{EN} = 0V, V_{VIN} = 13.5V$                                    |      |      | 1    | μA   |
| R <sub>PDEN</sub>                      | EN Pull Down Resistance                          | —   | 76   | 100  | 124  | kΩ   |
| Fault Protection                       |  |   |      |      |      |      |
| OTP                                    | Thermal Shutdown Threshold                       | $V_{VCC} = 3V$ to 5.5V  |      | 145  |      | °C   |
| OTP <sub>HYS</sub>                     | Thermal Shutdown Hysteresis                      | $V_{VCC} = 3V$ to 5.5V  | _    | 20   | _    | °C   |
| UVLO                                   | VIN Lockout Threshold                            | V <sub>VCC</sub> = 3V   | 0.25 | 0.35 | 0.45 | V    |
| <b>UVLO<sub>HYS</sub></b>              | V <sub>IN</sub> Lockout Hysteresis               | V <sub>VCC</sub> = 3V   | 20   | 40   | 70   | mV   |
| SCD                                    | Short-Circuit Protoction Threshold               | $V_{VCC} = 3.3V; V_{VIN} = 0.5V$                                  | 180  | 265  | 350  | mV   |
| SCP Short-Circuit Protection Threshold |  | V <sub>VCC</sub> = 3.3V; V <sub>VIN</sub> = 13.5V                 | 100  | 285  | 500  | mV   |



**Switching Characeristics** ( $T_A = +25^{\circ}C$ ,  $V_{TERM} = V_{VCC} = 5V$ ,  $R_{PG} = 100k\Omega$ ,  $R_{VOUT} = 10\Omega$ ,  $C_{VIN} = 1\mu$ F,  $C_{VOUT} = 0.1\mu$ F,  $C_{VCC} = 1\mu$ F,  $C_{SR} = 1$ nF, unless otherwise specified.)

| Symbol                                      | Parameter                    | Condition        | Min | Тур | Max   | Unit       |
|---|------------------------------|------------------|-----|-----|-------|------------|
| V <sub>VIN</sub> = 1.8V                     |                              |                  | •   |     |       |            |
|   | Output Turn On Delay Time    | $V_{VCC} = 3.3V$ | —   | 375 | —     |            |
| ton   | Output Turn-On Delay Time    | $V_{VCC} = 5V$   | —   | 370 | _     |            |
|   |                              | $V_{VCC} = 3.3V$ | —   | 0.5 | _     | μs         |
| LOFF  | Output Turn-Oil Delay Time   | $V_{VCC} = 5V$   | —   | 0.5 | _     |            |
|   | Bower Cood Turn on Time      | $V_{VCC} = 3.3V$ | —   | 1.4 | _     | <b>m</b> 0 |
| LPGON                                       | Fower Good Tulli-off Tillie  | $V_{VCC} = 5V$   | —   | 1.3 | _     | 1115       |
|   | Bower Cood Turn off Time     | $V_{VCC} = 3.3V$ | —   | 10  | _     | 20         |
| t <sub>PGOFF</sub> Power Good Turn-off Time | Fower Good Full-off Time     | $V_{VCC} = 5V$   | —   | 6   | _     | 115        |
|   | $V_{VCC} = 3.3V$             | —                | 9   | —   | k)//o |            |
| 55  |                              | $V_{VCC} = 5V$   | —   | 9   | —     | KV/S       |
| $V_{VIN} = 12V$                             |                              |                  |     |     |       |            |
| 4   | Output Turn On Dolov Time    | $V_{VCC} = 3.3V$ | —   | 340 | —     |            |
| LON   | Output runi-On Delay Time    | $V_{VCC} = 5V$   | —   | 330 | —     |            |
|   |                              | $V_{VCC} = 3.3V$ | —   | 0.5 | _     | μs         |
| LOFF  | Odiput Tulli-Oli Delay Tille | $V_{VCC} = 5V$   | —   | 0.4 | _     |            |
| <b>+</b>                                    | Bower Good Turn on Time      | $V_{VCC} = 3.3V$ | —   | 1.6 | —     | ms         |
| IPGON POwer Good Full-on Fille              | Fower Good Full-on Fille     | $V_{VCC} = 5V$   | —   | 1.5 | _     | 1115       |
| t <sub>PGOFF</sub> Power Good Turn-off Time | Power Good Turn off Time     | $V_{VCC} = 3.3V$ | —   | 10  | _     | 20         |
|   | Fower Good Full-on Time      | $V_{VCC} = 5V$   | —   | 8   | —     | 115        |
| SD  | Output Slow Pata             | $V_{VCC} = 3.3V$ | —   | 30  | _     | k)//c      |
| JR  | SR Output Siew Rate          | $V_{VCC} = 5V$   | —   | 31  | _     | - κv/s     |







## Performance Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)



VIN = 12V VIN = 1.8V 4 4.5 5 5.5



Bleed Leakage Current vs. Input Voltage

Supply Voltage (V)





**NEW PRODUCT** 



## Performance Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified. cont.)





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DML3009LDC Document number: DS39184 Rev. 3 - 2



## Performance Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified. cont.)





Turn ON Response



Turn OFF Response VCC = 5.0V, VEN = 3.3V to 0V













# **Application Information**

#### **General Description**

The DML3009LDC is a single-channel load switch with a controlled adjustable turn-on and integrated PG indicator in a 12-pin DFN30x30 package. The device contains an N-channel MOSFET that can operate over an input voltage range of 0.5V to 12V and can support a maximum continuous current of 10A. The wide-input voltage range and high-current capability enable the device to be used across multiple designs and end equipment.  $6m\Omega$  on-resistance minimizes the voltage drop across the load switch and power loss from the load switch.

The controlled rise time for the device greatly reduces inrush current by large bulk load capacitances thereby reducing or eliminating power supply droop. The adjustable slew rate through SR provides the design flexibility to trade off the inrush current and power up timing requirements. Integrated PG indicator notifies the system about the status of the load switch to facilitate seamless power sequencing. During shutdown, the device has very low leakage current thereby reducing unnecessary leakages for downstream modules during standby. The DML3009LDC also has an embedded  $100\Omega$  on-chip resistor on BLEED pin for quick discharge of the output when switch is disabled.

#### Enable Control

The DML3009LDC device allows for enabling the MOSFET in an active-high configuration. When the VCC supply pin has an adequate voltage applied, and the EN pin is at logic high level, the MOSFET is enabled. Similarly, when the EN pin is at logic low level, the MOSFET is disabled. An internal pull-down resistor to ground on the EN pin ensures that the MOSFET disables when not being driven.

#### **Power Sequencing**

The DML3009LDC device functions with any power sequence, but the output turn-on delay performance can vary from what is specified. To archive the specified performance, there are two recommended power sequences:

- 1.)  $V_{VCC} \rightarrow V_{VIN} \rightarrow V_{EN}$
- 2.)  $V_{VIN} \rightarrow V_{VCC} \rightarrow V_{EN}$

#### Load Bleed (Quick Discharge)

The DML3009LDC device has an internal bleed discharge device, which is used to bleed the charge off of the load to ground after the MOSFET is disabled. The bleed discharge device is enabled whenever the MOSFET is disabled. The MOSFET and the bleed device are never concurrently active.

The BLEED pin must be connected to  $V_{OUT}$  either directly or through an external resistor,  $R_{EXT}$ .  $R_{EXT}$  must not exceed 1K $\Omega$  and can be used to increase the total bleed resistance.

Care must be taken to ensure that the power dissipated across R<sub>BLEED</sub> is kept at safe level. The maximum continuous power that dissipates across R<sub>BLEED</sub> is 0.4W. R<sub>EXT</sub> can be used to decrease the amount of power dissipated across R<sub>BLEED</sub>.

#### Adjustable Rise Time (Slew Rate Control)

The DML3009LDC device has controlled rise time for inrush current control. A capacitor to ground on the SR pin adjusts the rise time. Without a capacitor on SR, the rise time is at its minimum for fastest timing. Equation 1 approximately shows the relationship between  $C_{SR}$ ,  $V_{IN}$ , and rise time,  $t_{R}$ .

$$t_R = K2C_{SR}\sqrt{V_{IN}} + K3\sqrt{2 + V_{IN}} + K4\sqrt{C_{SR}} - K5$$

Where  $t_R$  is the rise time (µs)

- V<sub>IN</sub> is the input voltage (V)
- K2, K3, K4, and K5 is constant where K2 = 0.067, K3 = 137, K4 = 6.7, K5 = 67
- C<sub>SR</sub> is the capacitance value on the SR pin (pF)



## Application Information (continued)

Table 1 contains rise time values measured on a typical device. Rise times shown below are only valid for the power-up sequence 1.

|              |   | Times vs SR Capacitor  |                       |                         |  |
|--------------|---|------------------------|-----------------------|-------------------------|--|
|              |   | Rise                   | Time                  |                         |  |
| CSR          | $V_{CC}$ = 5V, $C_L$ = 0.1µF, $R_L$ = 10 $\Omega$ , 25°C; Measure $V_{OUT}$ rising time from 10% to 90% $V_{VIN}$ |                        |                       |                         |  |
|              | V <sub>VIN</sub> = 13.5V  | V <sub>VIN</sub> = 12V | V <sub>VIN</sub> = 5V | V <sub>VIN</sub> = 1.8V |  |
| 0 (floating) | 371µs   | 346µs                  | 233µs                 | 142µs                   |  |
| 0.22nF       | 448µs   | 430µs                  | 318µs                 | 232µs                   |  |
| 0.47nF       | 646µs   | 615µs                  | 452µs                 | 262µs                   |  |
| 1nF          | 902µs   | 880µs                  | 750µs                 | 393µs                   |  |
| 2.2nF        | 1408µs  | 1370µs                 | 1028µs                | 585µs                   |  |
| 4 7nF        | 2040us  | 1935us                 | 1466us                | 958us                   |  |

#### Table1. Rise Times vs SR Capacitor

Note: An SR Capacitor less than 4.7nF for system success startup is recommended.

#### Power Good

The DML3009LDC device has a power good output (PG) that can be used to indicate when the gate of the MOSFET is driven high and the switch is on with the on-resistance close to its final value (full load ready). The PG pin is an active-high, open-drain output that requires an external pullup resistor, R<sub>PG</sub>, greater than or equal to 1K $\Omega$  to an external voltage source, V<sub>TERM</sub>, compatible with input levels of those devices connected to this pin. Equation 2 approximately shows the relationship between C<sub>SR</sub>, V<sub>IN</sub>, and PG turn-on time, t<sub>PG\_ON</sub>.

$$t_{PG\ ON} = t_R + K1$$

Where

- t<sub>PG\_ON</sub> is the PG turn-on time (μs)
- K1 is constant, which is K1 = 800

Table 2 contains PG turn-on time values measured on a typical device. PG turn-on times shown below are valid for the power-up sequence 1.

|                 |                          | PG ti   | urn-on time    |                         |  |
|-----------------|--------------------------|---|----------------|-------------------------|--|
| C <sub>SR</sub> |                          | $V_{CC} = 5V, C_L = 0.1 \mu F, R_L = 10 \Omega, R_{PG} = 10 K \Omega, 25^{\circ} C$ |                |                         |  |
|                 | V <sub>VIN</sub> = 13.5V | $V_{VIN} = 12V$   | $V_{VIN} = 5V$ | V <sub>VIN</sub> = 1.8V |  |
| 0 (floating)    | 1171µs                   | 1098µs  | 863µs          | 935µs                   |  |
| 0.22nF          | 1338µs                   | 1260µs  | 1148µs         | 982µs                   |  |
| 0.47nF          | 1464µs                   | 1455µs  | 1292µs         | 1102µs                  |  |
| 1nF             | 1702µs                   | 1630µs  | 1530µs         | 1293µs                  |  |
| 2.2nF           | 2248µs                   | 2210µs  | 1868µs         | 1425µs                  |  |
| 4.7nF           | 2840µs                   | 2685µs  | 2467us         | 1758µs                  |  |

The power good output can be used as the enable signal for other active-high devices in the system. This allows for guaranteed by design power sequencing and reduces the number of enable signals required from the system controller. If the power good feature is not used in the application, the PG pin must be tied to GND.

#### **Short-Circuit Protection**

The DML3009LDC device is equipped with short-circuit protection that is used to help protect the part and the system from a sudden high-current event, such as the output, V<sub>OUT</sub>, being shorted to ground. This circuitry is only active when the gate of MOSFET is fully charged.

Once active, the circuitry monitors the difference in the voltage on the  $V_{IN}$  pin and the voltage on the BLEED pin. In order for the  $V_{OUT}$  voltage to be monitored through the BLEED pin, it is required that BLEED pin be connected to  $V_{OUT}$  either directly or through a resistor,  $R_{EXT}$ , which should not exceed 1K $\Omega$ . With the BLEED pin connected to VOUT, the short-circuit protection is able to monitor the voltage drop across the MOSFET.

If the voltage drop across the MOSFET is greater than or equal to the short-circuit protection threshold voltage, the MOSFET is immediately turned off, and the load bleed is activated. The part remains latched in this off state until EN is toggled or VCC supply voltage is cycled at which point the MOSFET turns on delay and slew rate. The current through the MOSFET that causes a short-circuit event can be calculated by dividing the short-circuit protection threshold by expected on-resistance of the MOSFET



## Application Information (continued)

#### **Thermal Shutdown**

The DML3009LDC device has equipped thermal shutdown protection for internally or externally generated excessive temperatures. This circuitry is disabled when EN is not active to reduce standby current. When an overtemperature condition is detected, the MOSFET immediately turns off, and the load bleed is active.

The part comes out of thermal shutdown when the junction temperature decreases to a safe operating temperature as dictated by the thermal hysteresis. Upon exiting a thermal shutdown state and if EN remains active, the MOSFET turns on in a controlled fashion with the normal output turn-on delay and slew rate.

#### Undervoltage Lockout

The DML3009LDC device has equipped undervoltage lockout protection. DML3009LDC turns the MOSFET off and activates the load bleed when the input voltage. V<sub>IN</sub>, is less than or equal to the undervoltage lockout threshold. This circuitry is disabled when EN is not active to reduce standby current.

If the VIN voltage rise above the undervoltage lockout threshold and EN remains active, the MOSFET turns on in a controlled fashion with the normal output turn-on delay and slew rate.

#### **PCB Layout Consideration**

- 1. Place the input/output capacitors  $C_{VIN}$  and  $C_{VOUT}$  as close as possible to the  $V_{IN}$  and  $V_{OUT}$  pins.
- 2. The power traces, which are V<sub>IN</sub> trace, V<sub>OUT</sub> trace, and GND trace, should be short, wide, and direct for minimize parasitic inductance.
- 3. Place feedback resistance R<sub>BLEED</sub> as close as possible to BLEED pin.
- 4. The SR trace must be as short as possible to reduce parasitic capacitance.
- 5. Place C<sub>VCC</sub> capacitor near the device pin.
- 6. Connect the signal ground to the GND pin, and keep a single connection from GND pin to the power ground behind the input or output capacitors.
- For better power dissipation, via holes are recommended to connect the exposed pad's landing area to a large copper polygon on the other side of the PCB. The copper polygons and exposed pad shall connect to V<sub>IN</sub> pin on the printed circuit board.





# Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



|                      | V-DFN3030-12 |             |       |  |  |  |
|----------------------|--------------|-------------|-------|--|--|--|
|                      | Тур          | e B         |       |  |  |  |
| Dim                  | Min          | Min Max Typ |       |  |  |  |
| Α                    | 0.77         | 0.85        | 0.80  |  |  |  |
| A1                   | 0.00         | 0.05        | 0.02  |  |  |  |
| A3                   |              | -           | 0.203 |  |  |  |
| b                    | 0.20         | 0.30        | 0.25  |  |  |  |
| D                    | 2.95         | 3.05        | 3.00  |  |  |  |
| D2                   | 2.60         | 2.80        | 2.70  |  |  |  |
| Е                    | 2.95         | 3.05        | 3.00  |  |  |  |
| E2                   | 1.90         | 2.10        | 2.00  |  |  |  |
| е                    | 0            | ).50BSC     | )     |  |  |  |
| k                    |              |             | 0.20  |  |  |  |
| L                    | 0.25         | 0.35        | 0.30  |  |  |  |
| z                    |              |             | 0.125 |  |  |  |
| All Dimensions in mm |              |             |       |  |  |  |

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



## V-DFN3030-12 (Type B)

| Dimonsions | Value   |
|------------|---------|
| Dimensions | (in mm) |
| С          | 0.50    |
| X          | 0.32    |
| X1         | 0.45    |
| X2         | 2.86    |
| X3         | 2.82    |
| Y          | 0.48    |
| Y1         | 2.10    |
| Y2         | 3.30    |

# ne latest version.

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